

Process for Increasing Electrical Activation of Ion Implanted Dopants

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Technology Summary

A vacancy-generating dual-ion-implantation process enhances the electrical activation of a previously implanted dopant.

Inventor

HAYNES, TONY E

Condensed Matter Sciences Division

Licensing Contact

SIMS, DAVID L

UT-Battelle, LLC

Oak Ridge National Laboratory

Rm 124C, Bldg 4500N, MS: 6196

1 Bethel Valley Road

Oak Ridge, TN 37831

Office Phone: (865) 241-3808

E-mail: SIMSDL@ORNL.GOV

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